

# SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

# ATP301— General-Purpose Switching Device Applications

#### **Features**

- ON-resistance RDS(on)=57m $\Omega$  (typ.)
- · 10V drive

- Input capacitance Ciss=4000pF (typ.)
- · Halogen free compliance

## **Specifications**

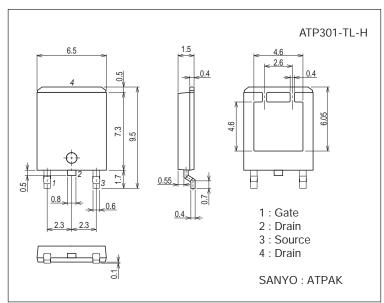
#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-100	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-28	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-112	А
Allowable Power Dissipation	PD	Tc=25°C	70	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		54	mJ
Avalanche Current *2	IAV		-28	А

Note :\*1  $V_{DD}$ =-30V, L=100 $\mu$ H,  $I_{AV}$ =-28A

## **Package Dimensions**

unit : mm (typ) 7057-001



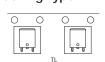
# **Product & Package Information**

• Package : ATPAK

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

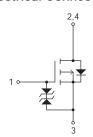
#### Packing Type: TL



# Marking



#### **Electrical Connection**



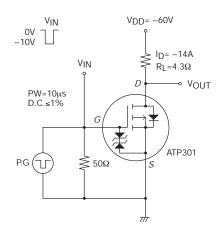
http://semicon.sanyo.com/en/network

<sup>\*2</sup> L≤100µH, Single pulse

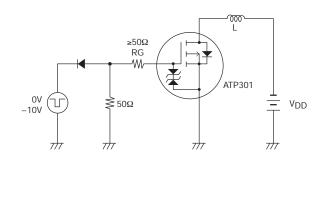
# Electrical Characteristics at Ta=25°C

Parameter	Cumhal	Conditions	Ratings			Unit
Parameter	Symbol	Conditions	min	typ	max	Ullit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-100			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-2.0		-3.5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =-10V, I <sub>D</sub> =-14A		32		S
Static Drain-to-Source On-State Resistance	RDS(on)	ID=-14A, VGS=-10V		57	75	mΩ
Input Capacitance	Ciss			4000		pF
Output Capacitance	Coss	V <sub>DS</sub> =-20V, f=1MHz		270		pF
Reverse Transfer Capacitance	Crss			150		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			32		ns
Rise Time	tr	See specified Test Circuit		130		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		330		ns
Fall Time	tf			190		ns
Total Gate Charge	Qg			73		nC
Gate-to-Source Charge	Qgs	V <sub>D</sub> S=-60V, V <sub>G</sub> S=-10V, I <sub>D</sub> =-28A		16		nC
Gate-to-Drain "Miller" Charge	Qgd			14		nC
Diode Forward Voltage	VSD	IS=-28A, VGS=0V		-1.0	-1.5	V

# **Switching Time Test Circuit**

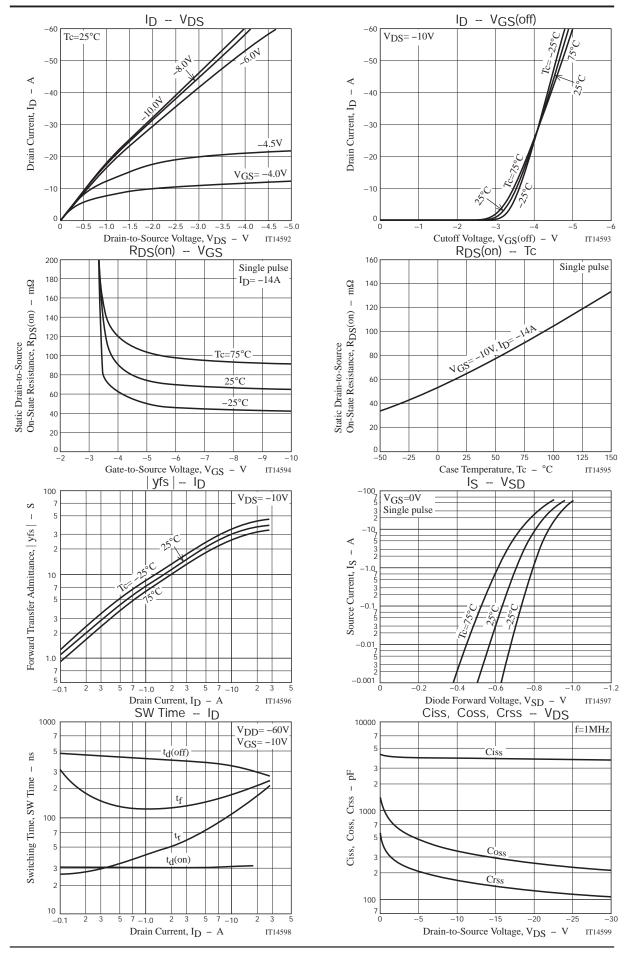


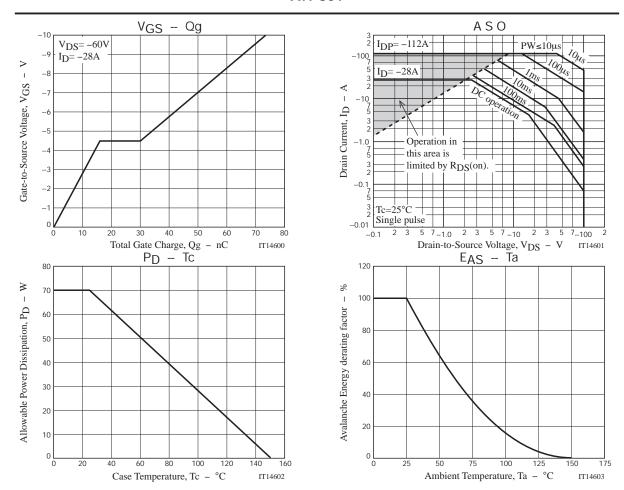
# **Avalanche Resistance Test Circuit**



# **Ordering Information**

Device	Package Shipping		memo	
ATP301-TL-H ATPAK		3,000pcs./reel	Pb Free and Halogen Free	



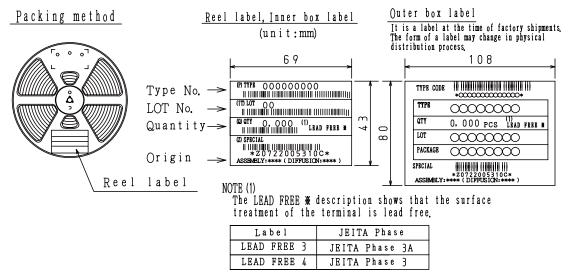


#### **Taping Specification**

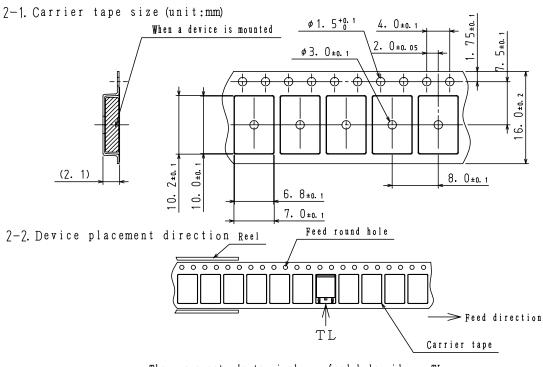
ATP301-TL-H

## 1. Packing Format (TL)

Package Name Carrier		Maximum Number of devices contained (pcs)			Packing format		
Lacrage Mame	Туре	Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18	
					1 reels contained	5 inner boxes contained	
ATPAK	ATP	rp  3,000 3,00	3,000	, 000 15, 000	Dimensions:mm (external)	Dimensions:mm (external)	
					340×340×28	355×355×165	



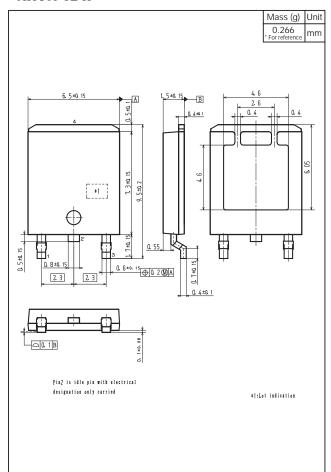
# 7. Taping configuration



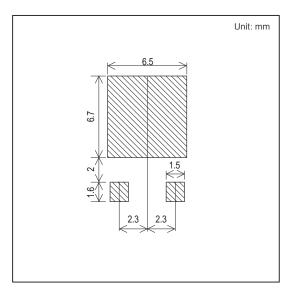
The one erectrode terminals on feed hole side····TL

# **Outline Drawing**

# ATP301-TL-H



## **Land Pattern Example**



Note on usage: Since the ATP301 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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